

MOSFETs Silicon Carbide N-Channel MOS

### TW107N65C

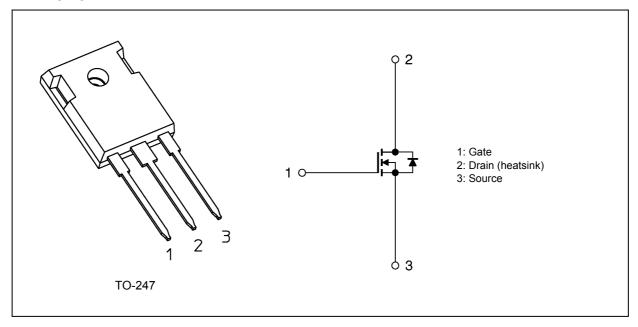
### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage:  $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage:  $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 107 \text{ m}\Omega$  (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage:  $V_{th}$  = 3.0 to 5.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.2 mA)
- (6) Enhancement mode.

### 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics	Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	650	V
Gate-source voltage		$V_{GSS}$	+25/-10	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	I <sub>D</sub>	20	Α
Drain current (DC)	( T <sub>c</sub> = 100°C )	I <sub>D</sub>	16	
Drain current (pulsed)	$(T_c = 25  ^{\circ}C)$	I <sub>DP</sub>	45	
Drain current (pulsed)	( T <sub>c</sub> = 100°C )	I <sub>DP</sub>	35	
Power dissipation	( T <sub>c</sub> = 25°C )	P <sub>D</sub>	76	W
Channel temperature		T <sub>ch</sub>	175	℃
Storage temperature		T <sub>stg</sub>	-55 to 175	
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.950	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note1: Ensure that the channel temperature does not exceed 175 °C.

Caution:This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = +25/-10 V, V <sub>DS</sub> = 0 V	_	_	±0.1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	_	2	25	
		T <sub>a</sub> = 150 °C, V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V		10	ı	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 4 mA, V <sub>GS</sub> = 0 V	650	_	_	V
Gate threshold voltage (Note2	) V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.2 mA	3.0	_	5.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 18 V, I <sub>D</sub> = 10 A	_	107	145	mΩ
		T <sub>a</sub> = 150 °C, V <sub>GS</sub> = 18 V, I <sub>D</sub> = 10 A	_	127	_	

Note2: Please be sure to apply  $I_{GSS}$  ( $V_{GS}$  = 25 V) before the  $V_{th}$  test.

# 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V,	_	600	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 100 kHz	_	3.7	_	
Output capacitance	C <sub>oss</sub>	]		80	_	
Output charge	Q <sub>oss</sub>		_	51	_	nC
C <sub>oss</sub> stored energy	E <sub>oss</sub>	1	_	7.2	_	μJ
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	11	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	32	_	ns
Switching time (turn-on time)	t <sub>on</sub>	1	_	56	_	
Switching time (fall time)	t <sub>f</sub>	1	_	25	_	
Switching time (turn-off time)	t <sub>off</sub>	]	_	56	_	

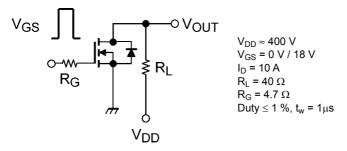


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$ $I_{D} = 10 \text{ A}$	1	21	ı	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	12	_	
Gate-drain charge	$Q_{gd}$		_	2.3	_	



# 6.4. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note3)	I <sub>DR</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	18	Α
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	_	_	12	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	20	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	16	
Reverse drain current	(Note3)	I <sub>DRP</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	45	
(pulsed)			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	_	_	27	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	45	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	35	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = -5 V	_	-1.35	-1.80	V
			T <sub>a</sub> = 150 °C, I <sub>DR</sub> = 5 A, V <sub>GS</sub> = -5 V	_	-1.60	_	
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V,	_	38	_	ns
Reverse recovery charge		Q <sub>rr</sub>	$V_{DD} = 400 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$	_	137	_	nC
Peak reverse recovery current		I <sub>rr</sub>		_	7.2	_	А

Note3: Ensure that the channel temperature does not exceed 175  $^{\circ}\text{C}$ .

Rev.1.0



### 7. Marking (Note)

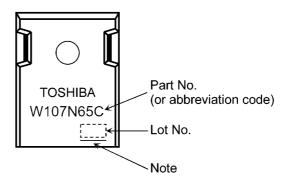


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the

restriction of the use of certain hazardous substances in electrical and electronic equipment.



#### 8. Characteristics Curves (Note)

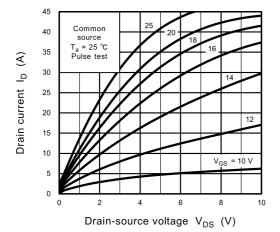


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

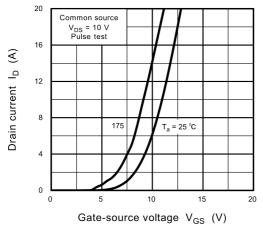


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

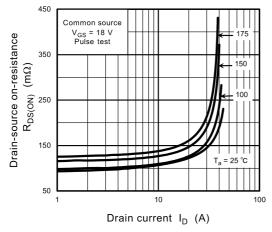


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

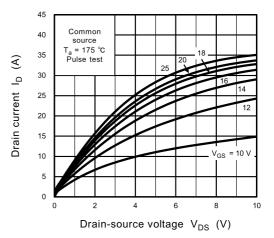


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

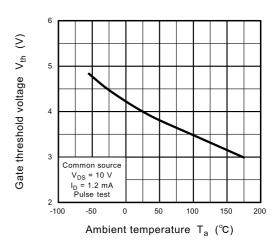


Fig. 8.4 V<sub>th</sub> - T<sub>a</sub>

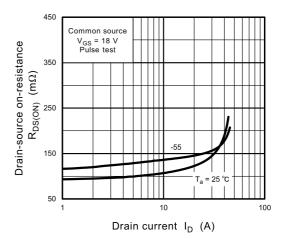


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>



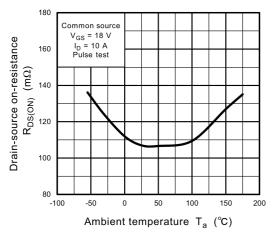


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

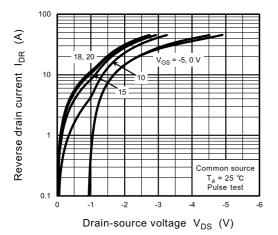


Fig. 8.9 IDR - VDS

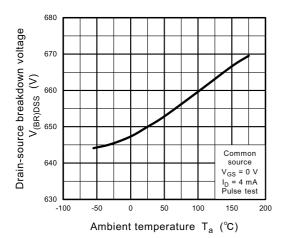


Fig. 8.11 V<sub>DSS</sub> - T<sub>a</sub>

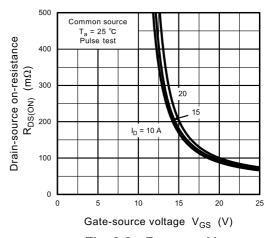


Fig. 8.8 R<sub>DS(ON)</sub> - V<sub>GS</sub>

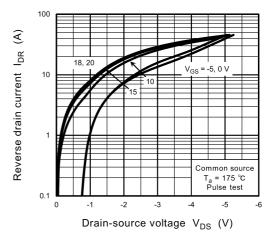


Fig. 8.10 I<sub>DR</sub> - V<sub>DS</sub>

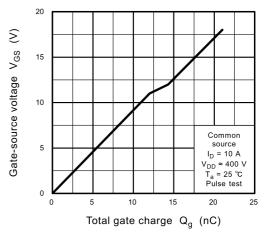
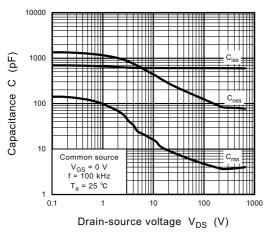


Fig. 8.12 Dynamic Input Characteristics





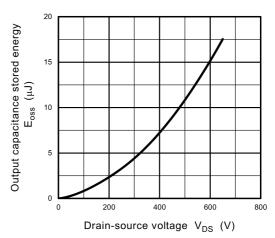
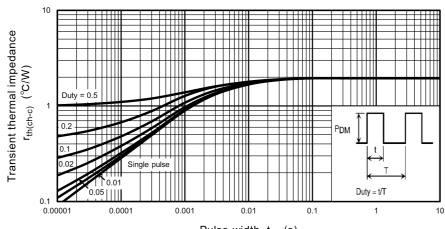


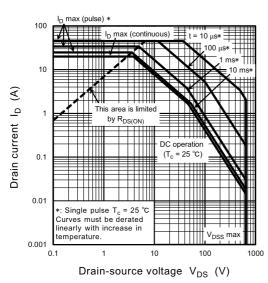
Fig. 8.13 C - V<sub>DS</sub>

Fig. 8.14 E<sub>oss</sub> - V<sub>DS</sub>



Pulse width  $t_w$  (s)

Fig. 8.15  $r_{th(ch-c)} - t_w$  (Guaranteed Maximum)



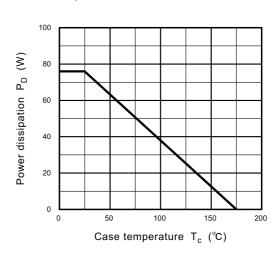


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

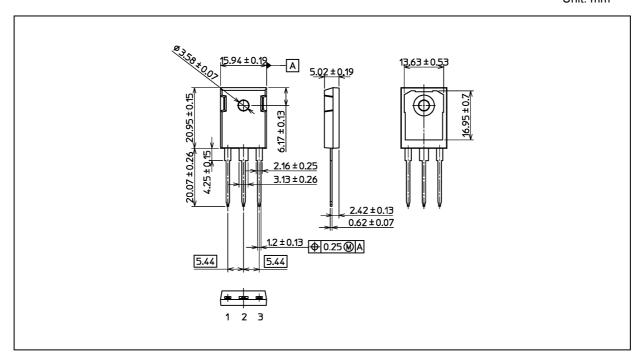
Fig. 8.17 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)
TOSHIBA: 2-16L1A
Nickname: TO-247



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